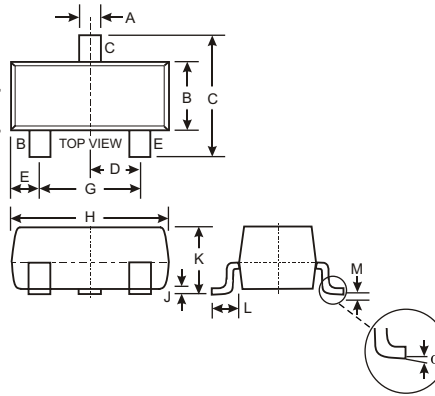


### Features

- Ideally Suited for Automatic Insertion
- Complementary NPN Types Available (BC846-BC848)
- For Switching and AF Amplifier Applications

### Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Pin Connections: See Diagram
- Marking Codes (See Table Below & Diagram on Page 3)
- Ordering & Date Code Information: See Page 3
- Approx. Weight: 0.008 grams



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.85	0.80
α	0°	8°
All Dimensions in mm		

Marking Code (Note 2)			
Type	Marking	Type	Marking
BC856A	3A, K3A	BC857C	3G, K3G
BC856B	3B, K3B	BC858A	3J, K3J, K3A, K3V
BC857A	3E, K3V, K3A	BC858B	3K, K3K, K3B, K3W
BC857B	3F, K3W, K3B	BC858C	3L, K3L, K3G

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-80 -50 -30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-65 -45 -30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-100	mA
Peak Collector Current	I <sub>CM</sub>	-200	mA
Peak Emitter Current	I <sub>EM</sub>	-200	mA
Power Dissipation (Note 1)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. Current gain subgroup "C" is not available for BC856.

**Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage (Note 3)	BC856 BC857 BC858	V <sub>(BR)CBO</sub>	-80 -50 -30	— — —	— — —	V	I <sub>C</sub> = 10μA, I <sub>B</sub> = 0	
Collector-Emitter Breakdown Voltage (Note 3)	BC856 BC857 BC858	V <sub>(BR)CEO</sub>	-65 -45 -30	— — —	— — —	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	
Emitter-Base Breakdown Voltage (Note 3)		V <sub>(BR)EBO</sub>	-5	—	—	V	I <sub>E</sub> = 1μA, I <sub>C</sub> = 0	
H-Parameters								
Small Signal Current Gain	Current Gain Group A B C	h <sub>fe</sub>	— — —	200 330 600	— — —	—	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA, f = 1.0kHz	
Input Impedance	Current Gain Group A B C	h <sub>ie</sub>	— — —	2.7 4.5 8.7	— — —	kΩ kΩ kΩ		
Output Admittance	Current Gain Group A B C	h <sub>oe</sub>	— — —	18 30 60	— — —	μS μS μS		
Reverse Voltage Transfer Ratio	Current Gain Group A B C	h <sub>re</sub>	— — —	1.5x10 <sup>-4</sup> 2x10 <sup>-4</sup> 3x10 <sup>-4</sup>	— — —	— — —		
DC Current Gain (Note 3)	Current Gain Group A B C	h <sub>FE</sub>	125 220 420	180 290 520	250 475 800	—		V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Collector-Emitter Saturation Voltage (Note 3)		V <sub>CE(SAT)</sub>	—	-75 -250	-300 -650	mV		I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage (Note 3)		V <sub>BE(SAT)</sub>	—	-700 -850	—	mV		I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage (Note 3)		V <sub>BE(ON)</sub>	-600 —	-650 —	-750 -820	mV		V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA
Collector-Cutoff Current (Note 3)	BC856 BC857 BC858	I <sub>CES</sub>	— — —	— — —	-15 -15 -15	nA nA nA		V <sub>CE</sub> = -80V V <sub>CE</sub> = -50V V <sub>CE</sub> = -30V
		I <sub>CBO</sub>	— —	— —	-15 -4.0	nA μA		V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = 150°C
Gain Bandwidth Product		f <sub>T</sub>	100	200	—	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 100MHz	
Collector-Base Capacitance		C <sub>CBO</sub>	—	3	—	pF	V <sub>CB</sub> = -10V, f = 1.0MHz	
Noise Figure		NF	—	2	10	dB	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = 200μA, R <sub>S</sub> = 2kΩ, f = 1kHz, Δf = 200Hz	

Notes: 3. Short duration pulse test used to minimize self-heating effect.

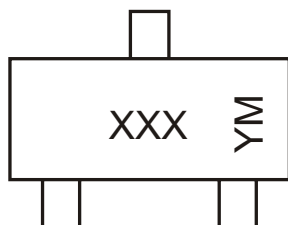
## Ordering Information (Note 4)

Device	Packaging	Shipping
BC85xx-7*	SOT-23	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

\*xx = device type, e.g. BC856A-7.

## Marking Information



XXX = Product Type Marking Code (See Page 1), e.g. K3A = BC856A

YM = Date Code Marking

Y = Year ex: N = 2002

M = Month ex: 9 = September

### Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004
Code	J	K	L	M	N	P	R

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D